

FIG. 1
(PRIOR ART)

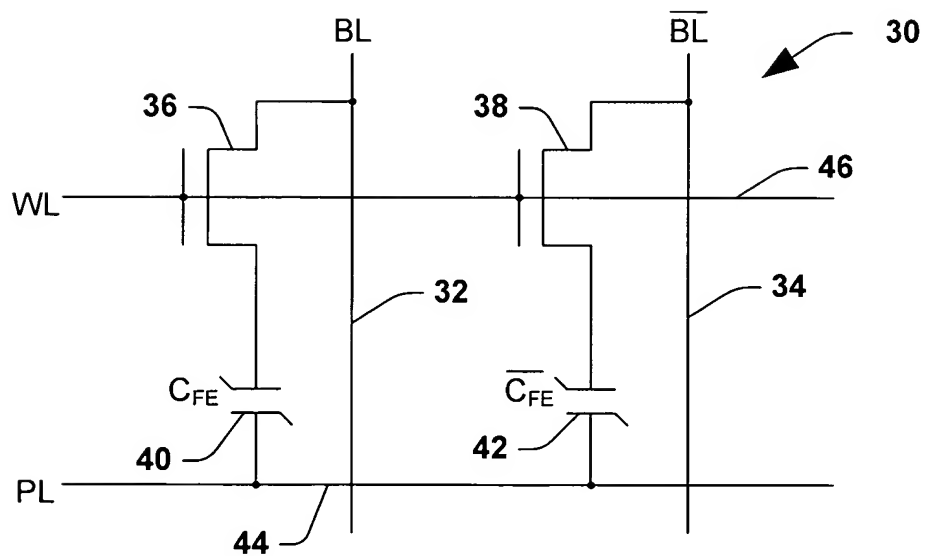


FIG. 2
(PRIOR ART)

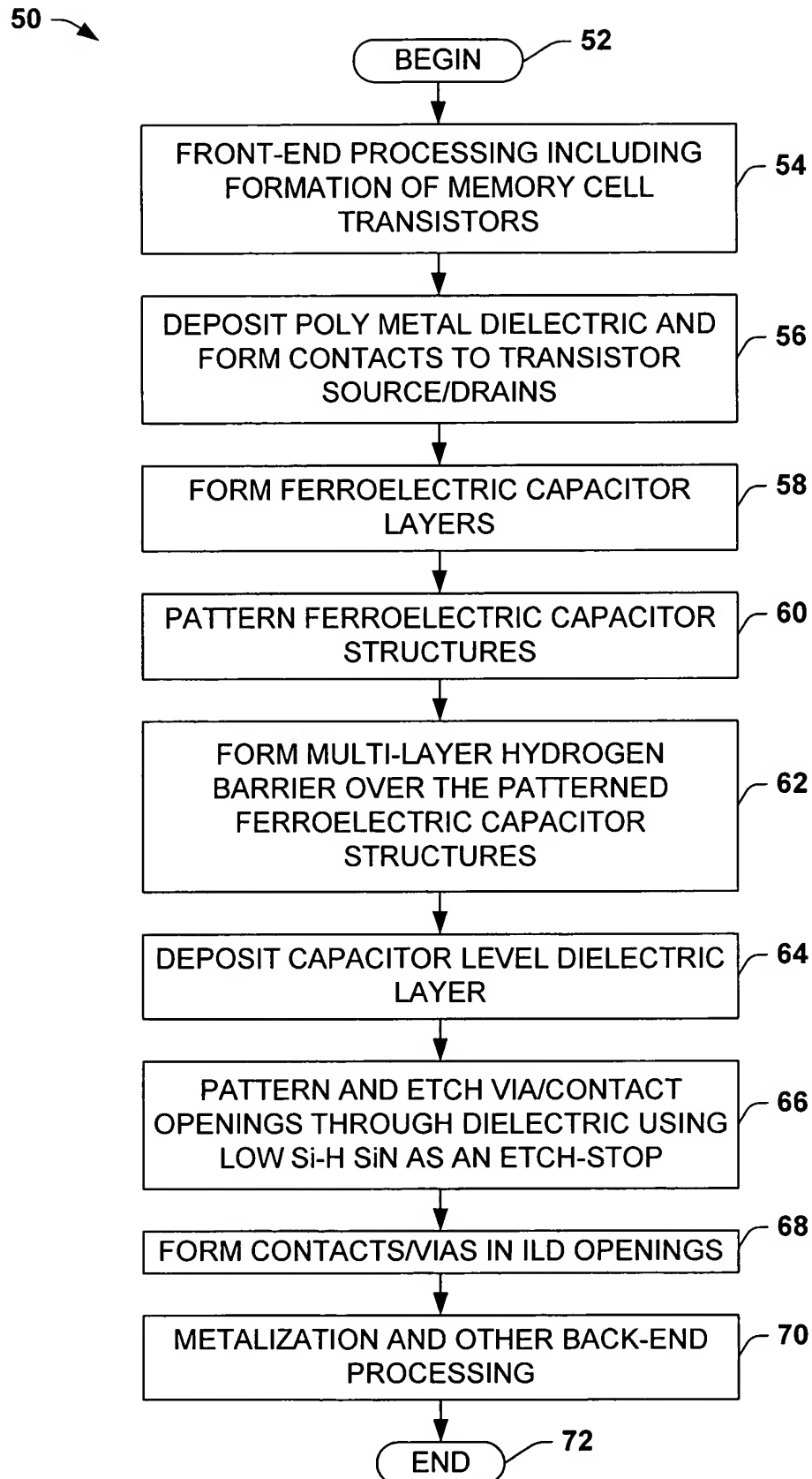


FIG. 3

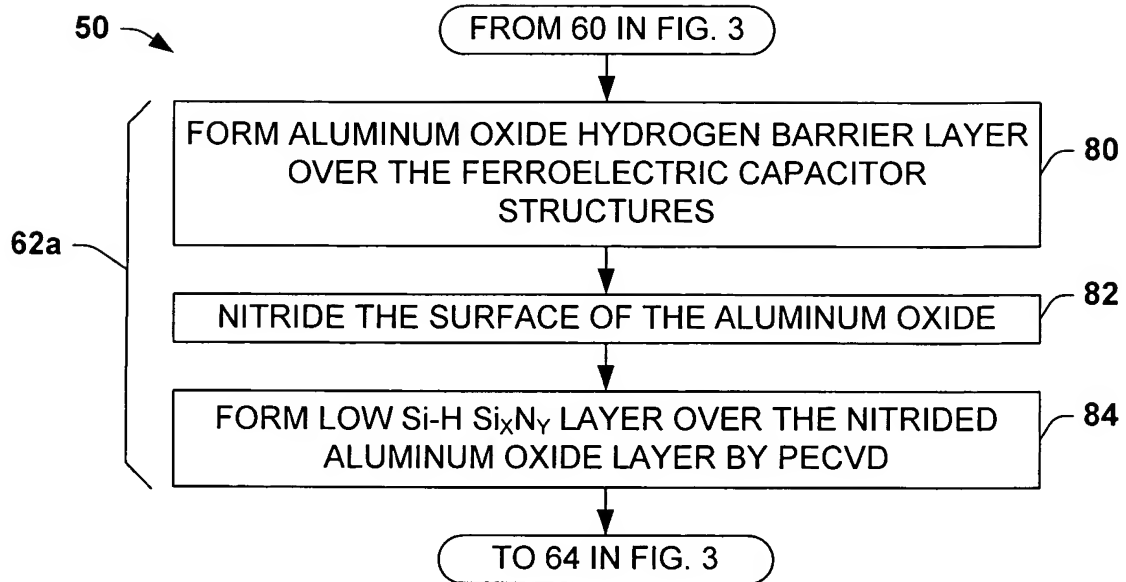


FIG. 4A

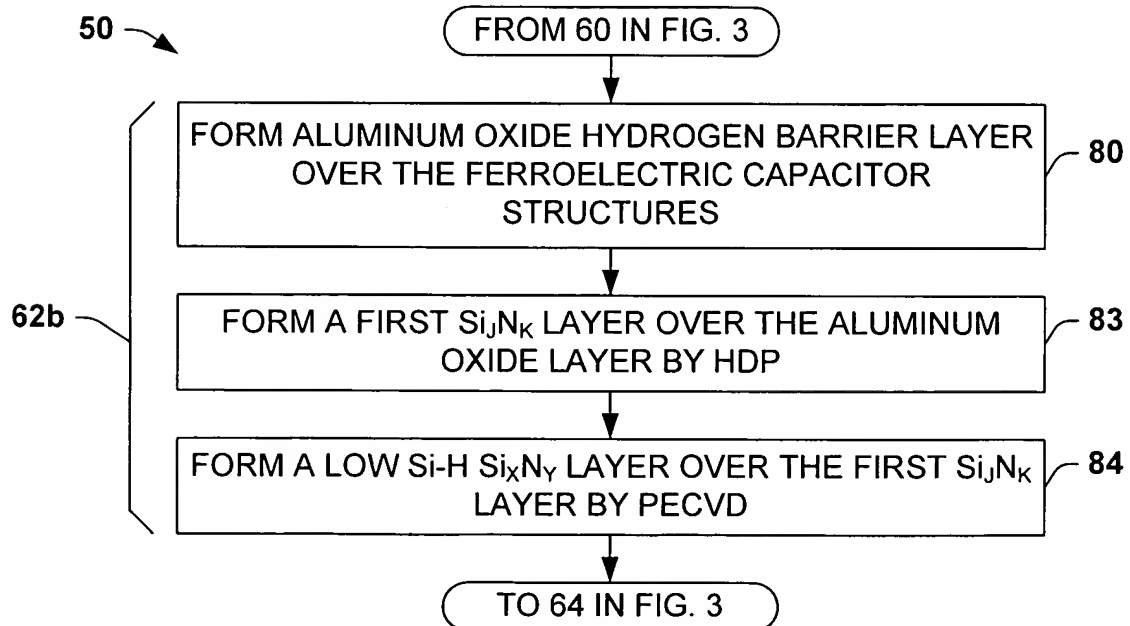


FIG. 4B

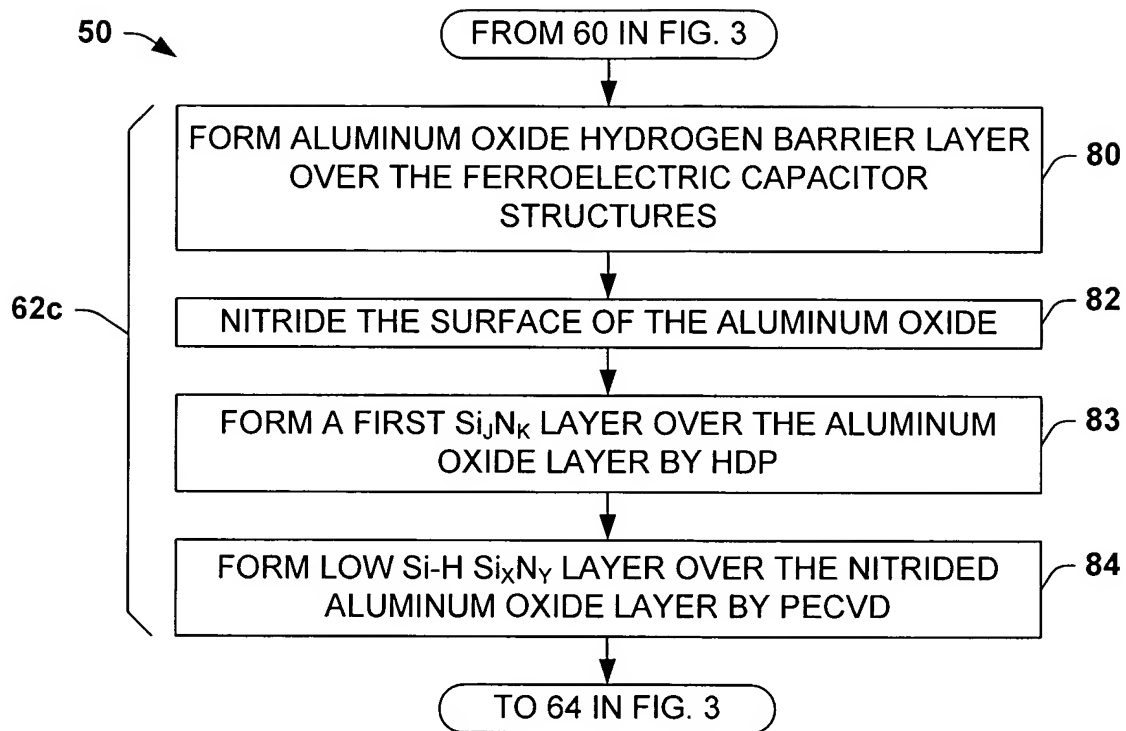


FIG. 4C

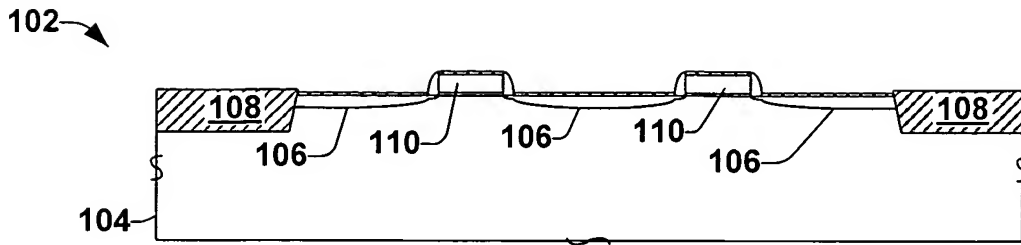


FIG. 5A

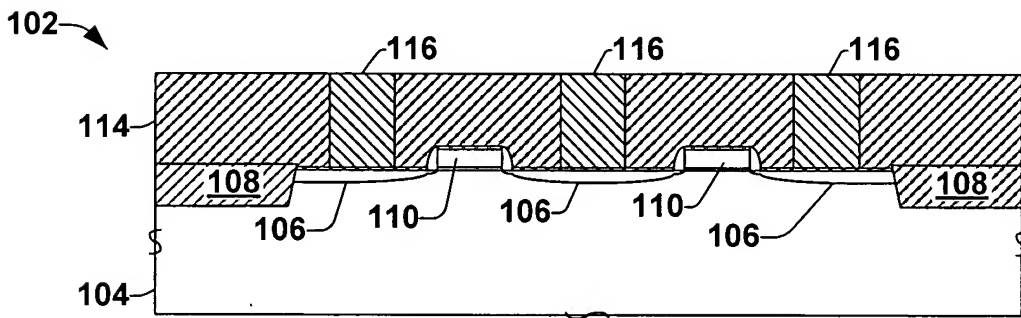


FIG. 5B

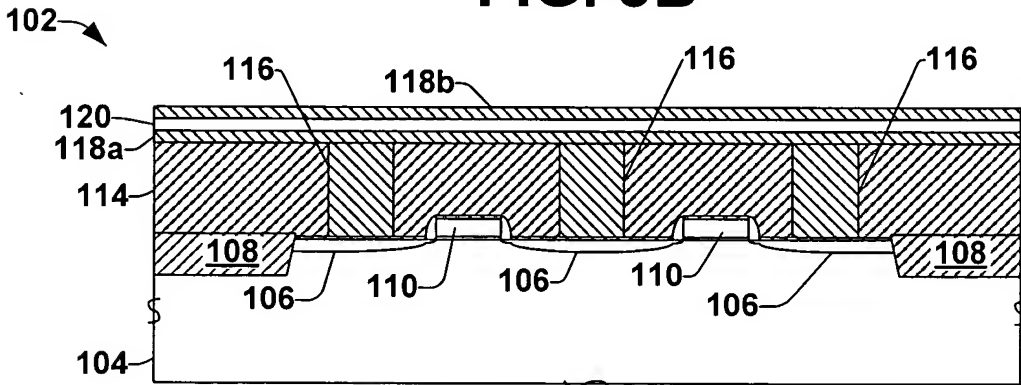


FIG. 5C

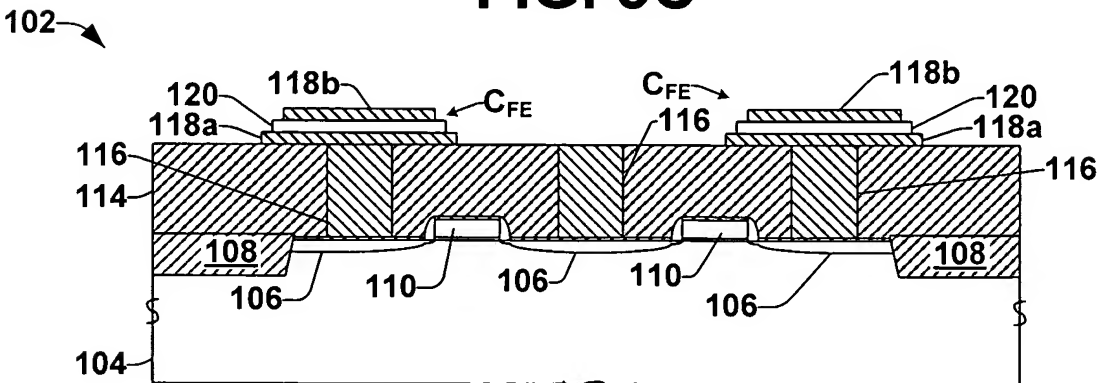


FIG. 5D

[illegible]

FIG. 10 shows two cross-sectional views of the semiconductor device during a fourth etching process. The left view shows the device after etching the first layer 118a, with the second layer 118b exposed. The right view shows the device after etching the second layer 118b, with the third layer 120 exposed. Labels include 102, 113, 115, 118a, 118b, 120, 114, AIOx, NITRIDED AIOx, and CFE.

FIG. 5H

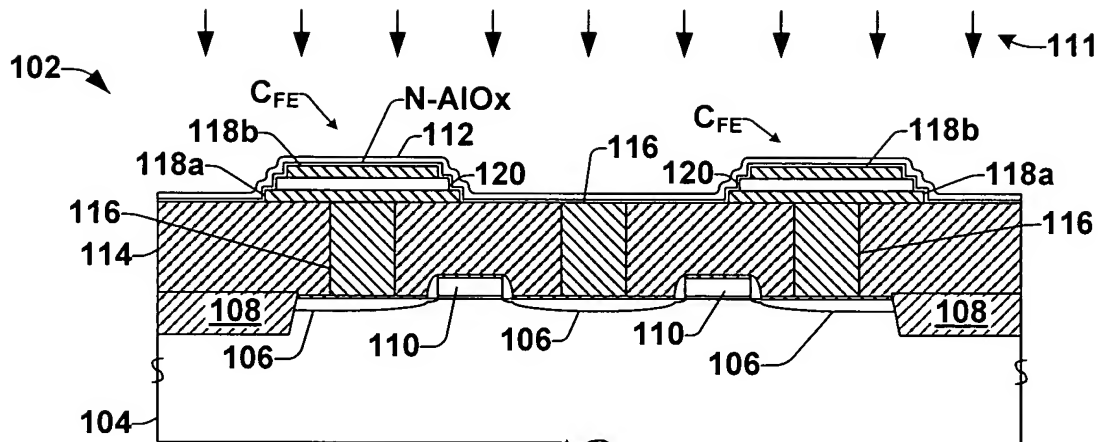


FIG. 5I

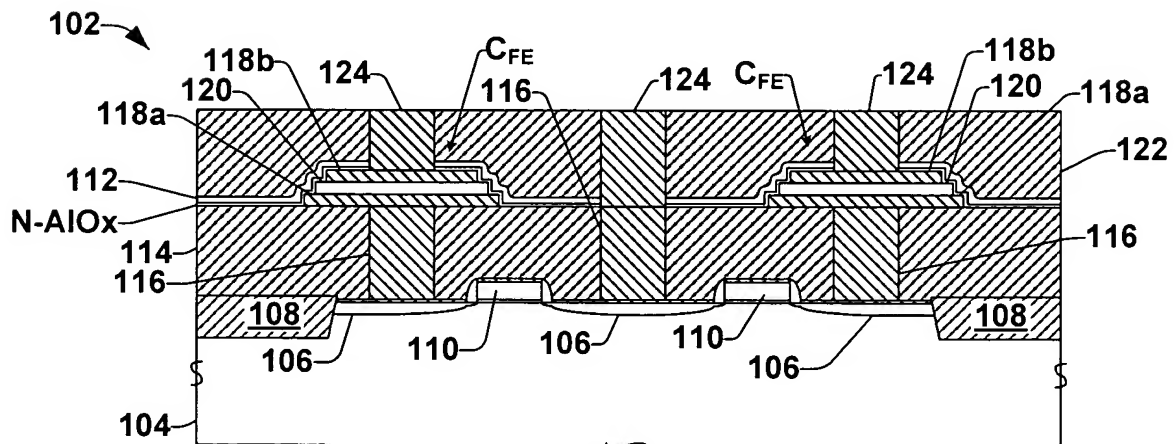


FIG. 5J

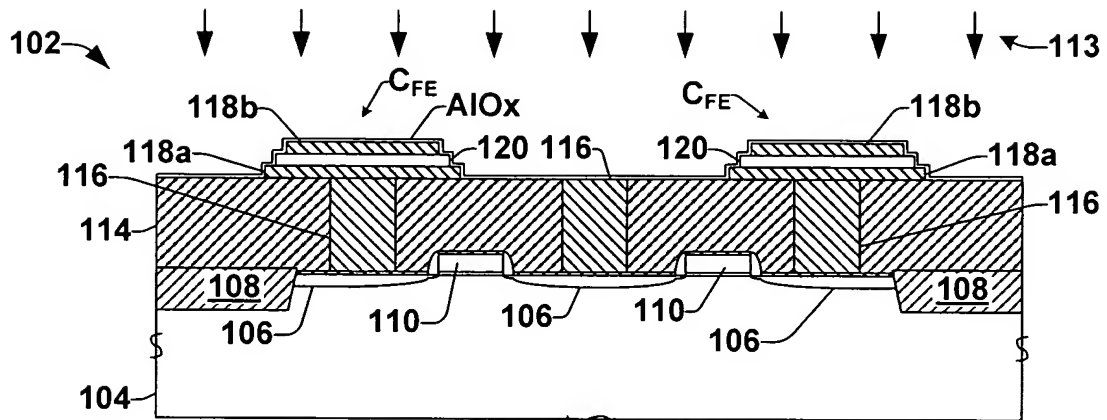


FIG. 5K

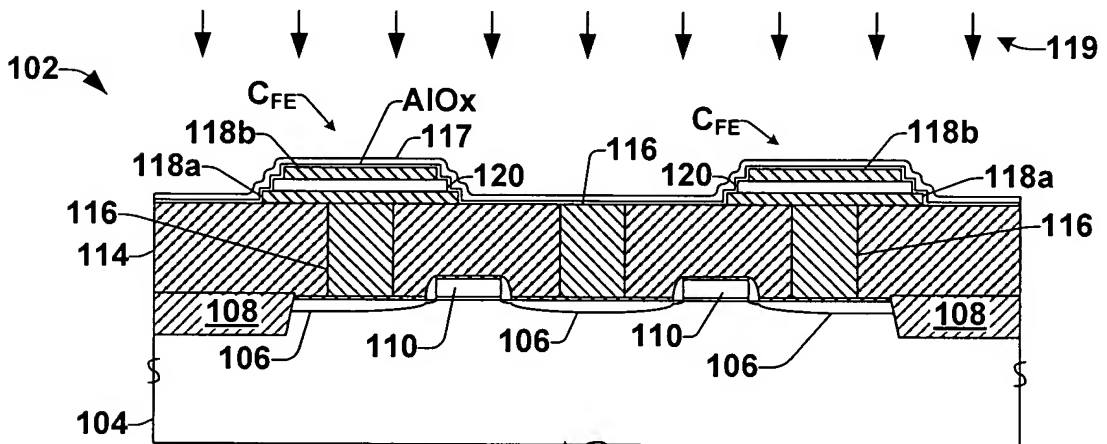


FIG. 5L

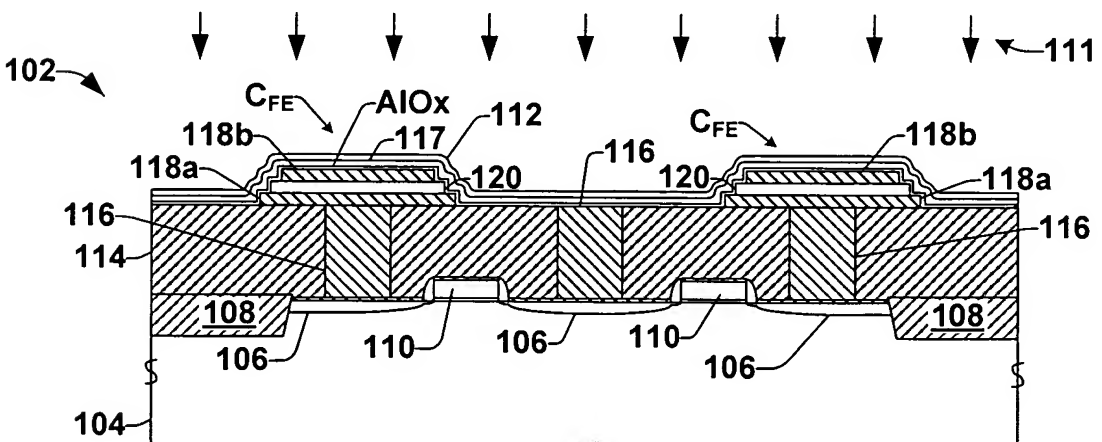


FIG. 5M

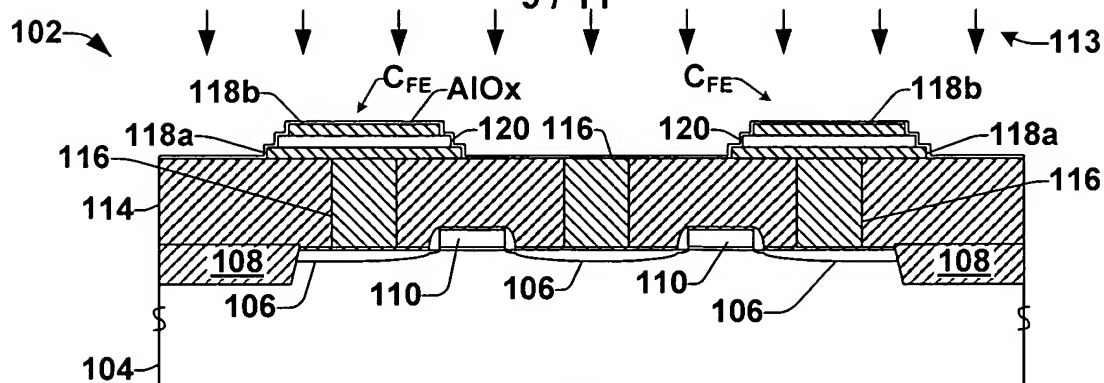


FIG. 5N

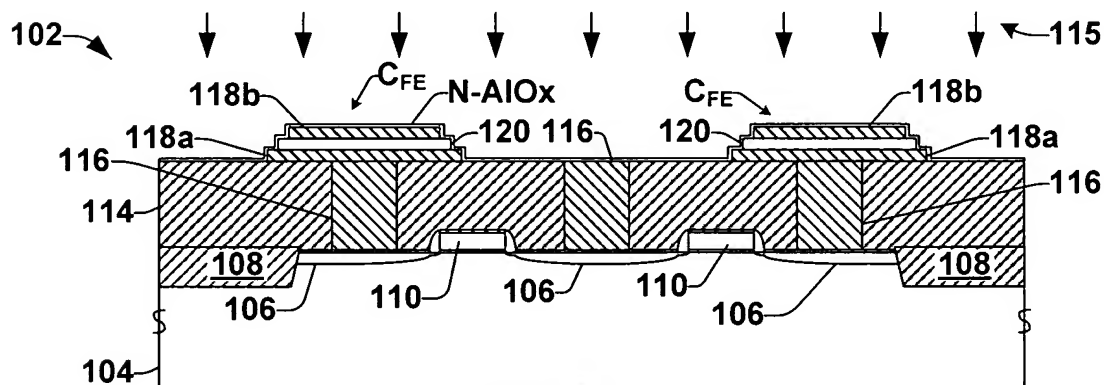


FIG. 50

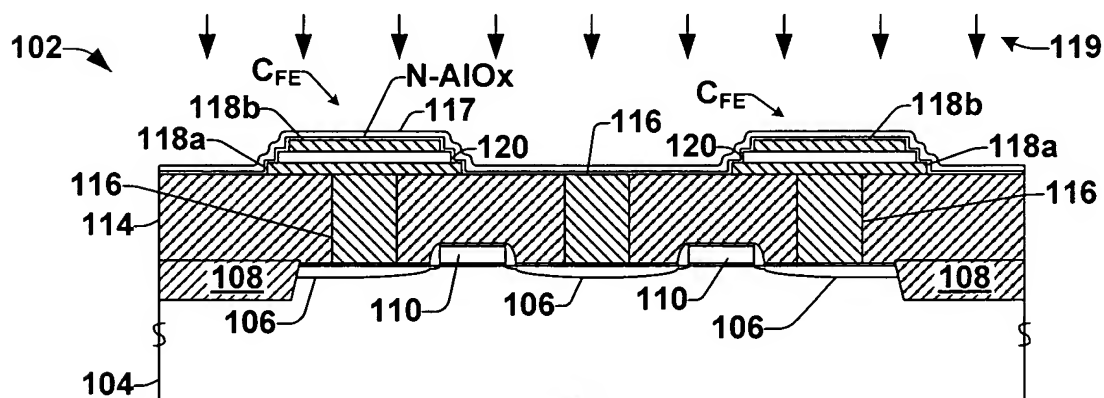


FIG. 5P

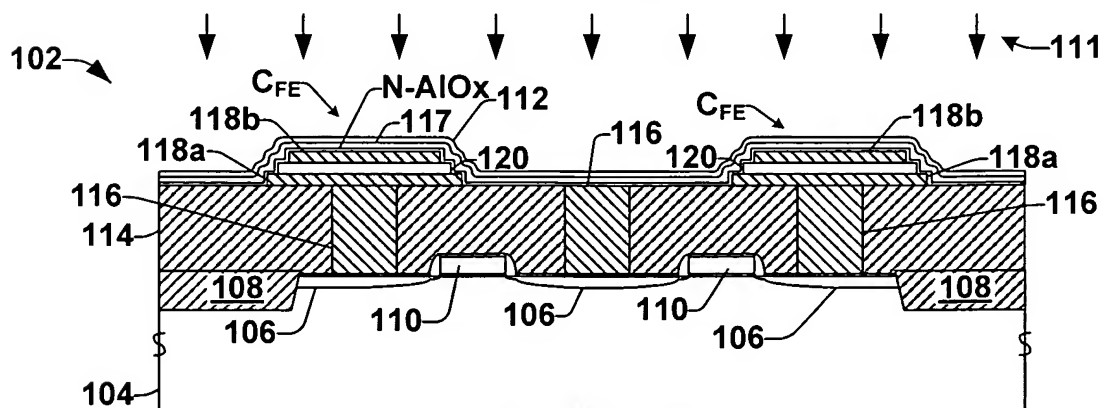


FIG. 5Q

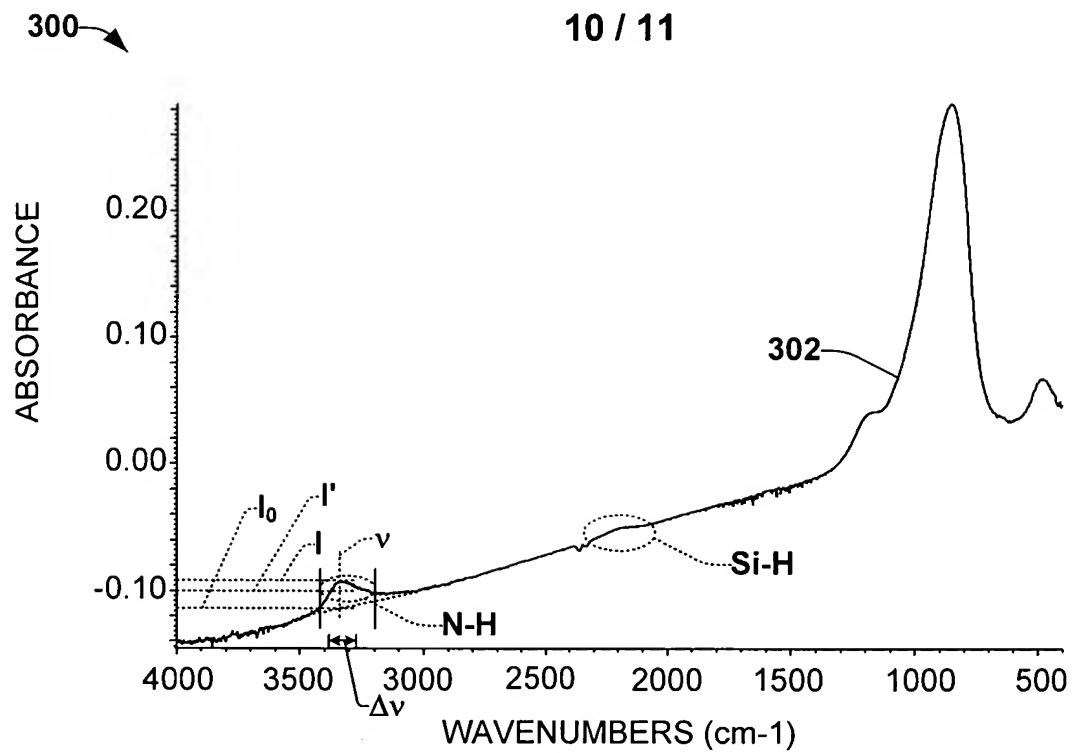


FIG. 6

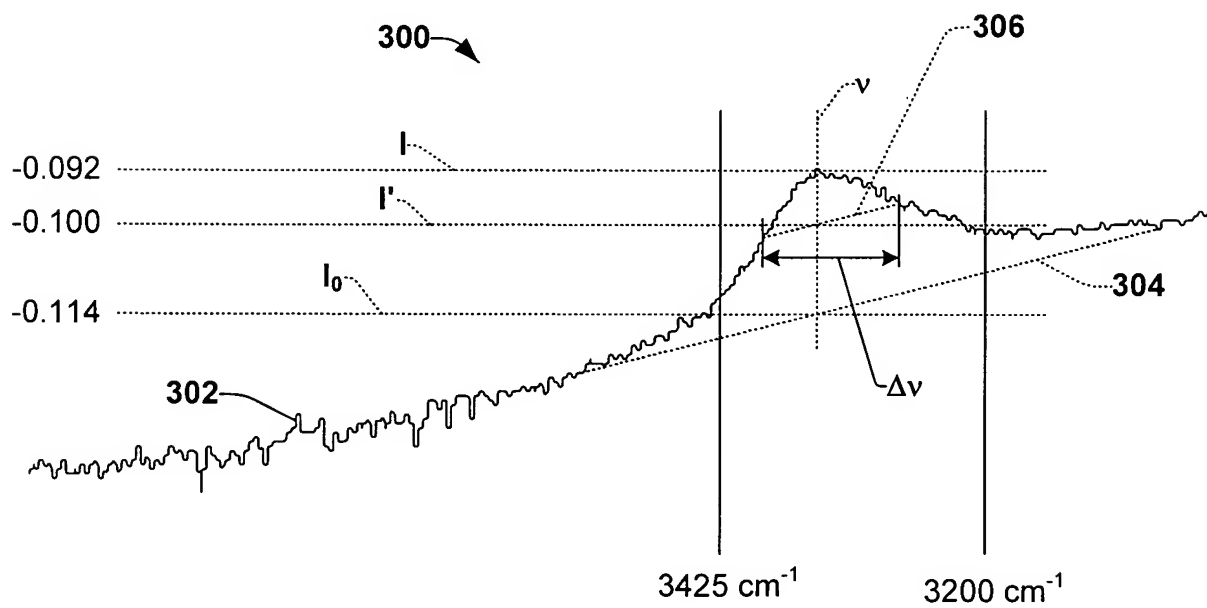


FIG. 7

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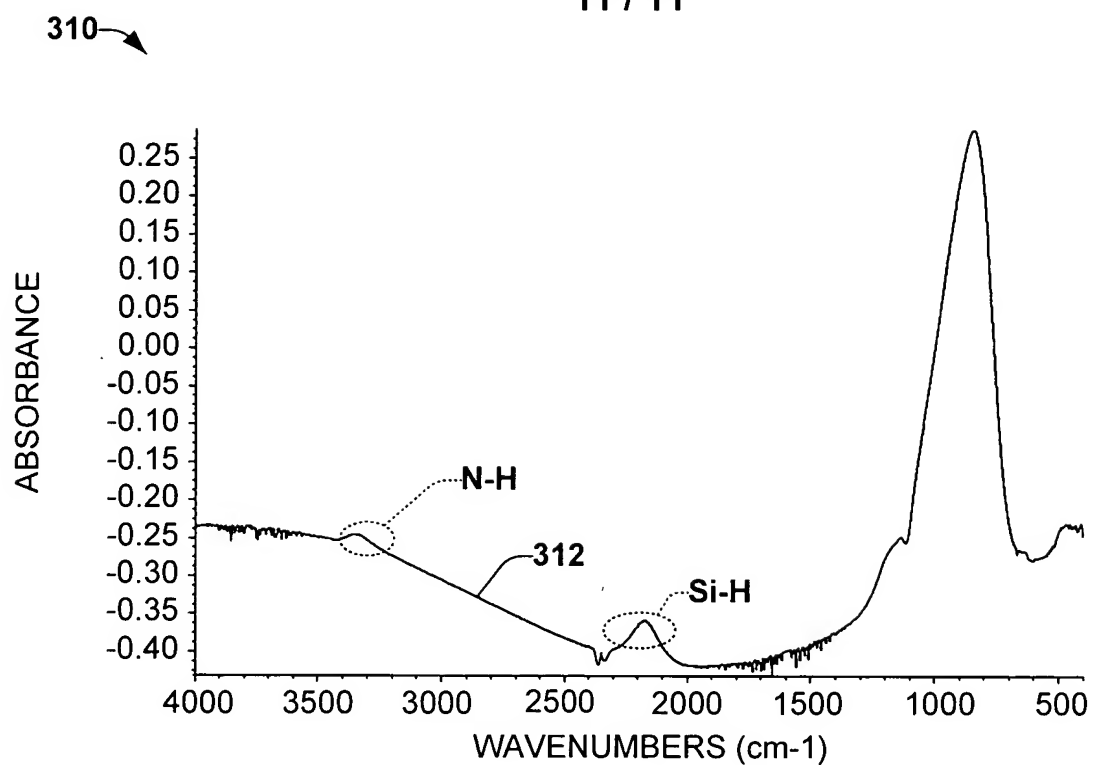


FIG. 8A

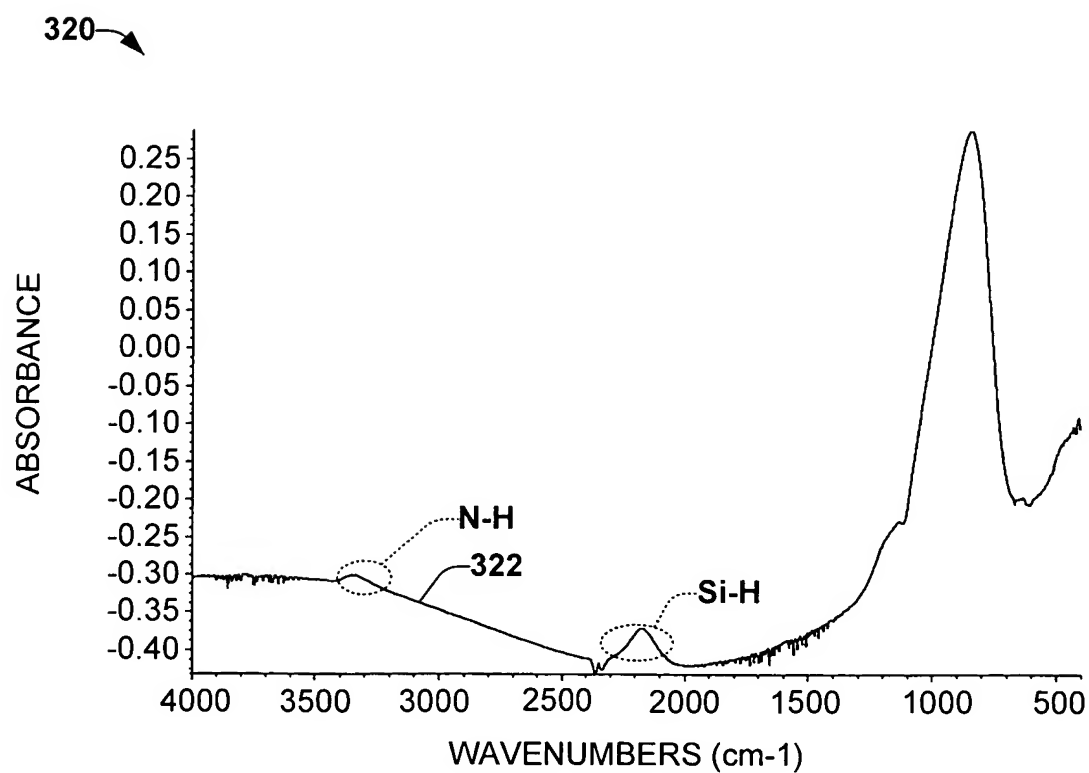


FIG. 8B